



TO-92 Plastic-Encapsulated Transistors

2SA673 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.4 \text{ W (Tamb=25°C)}$$

Collector current

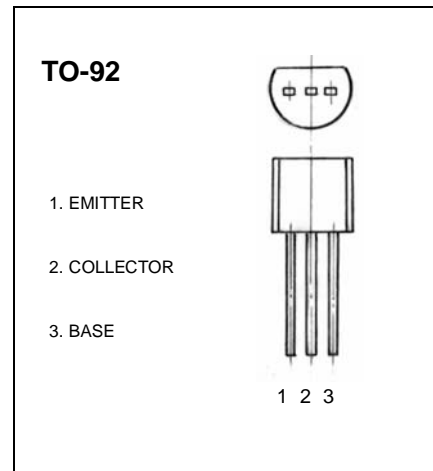
$$I_{CM} : -0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -35 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			-0.5	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE} = -3\text{V}, I_C = -10\text{mA}$	60		320	
	$h_{FE(2)}$	$V_{CE} = -3 \text{ V}, I_C = -500\text{mA}$	10			
Collector-emitter saturation voltage	V_{CEsat}^*	$I_C = -150\text{mA}, I_B = -15\text{mA}$			-0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = -3 \text{ V}, I_C = -10\text{mA}$			-0.75	V

*Measured using pulse

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	60-120	100-200	160-320